Abstracts

0.25-/spl mu/m BiCMOS receivers for normal and micro GSM900 and DCS 1800 base stations

P. Gould, Jenshan Lin, O. Boric-Lubecke, C. Zelley, Yung-Jinn Chen and Ran-Hong Yan. "0.25-/spl mu/m BiCMOS receivers for normal and micro GSM900 and DCS 1800 base stations." 2002 Transactions on Microwave Theory and Techniques 50.1 (Jan. 2002, Part II [T-MTT] (Special Issue on Silicon-Based RF and Microwave Integrated Circuits)): 369-376.

This paper describes two integrated RF receivers with low noise and high linearity for GSM900 and DCS1800 base stations. The chips were fabricated using a 0.25-/spl mu/m BiCMOS process. This is the first silicon-integrated radio front-end that can be used to meet GSM normal and micro base-station specifications reported to date. Noise figure, gain, and output third-order intercept point are 2.1 dB, 25.8 dB, and 25.7 dBm for GSM900 and 3.3 dB, 21.3 dB, and 22.5 dBm for DCS1800, respectively.

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